

TOSHIBA PHOTOCOUPLER GaAs IRED & PHOTO-TRANSISTOR

TLP621, TLP621-2, TLP621-4

PROGRAMMABLE CONTROLLER

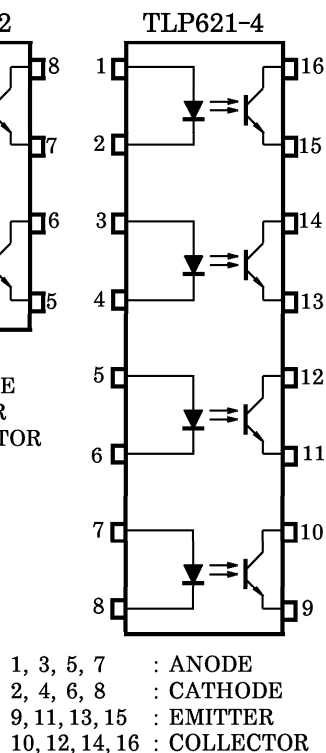
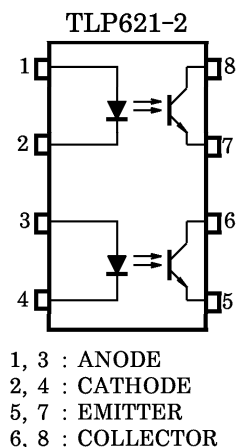
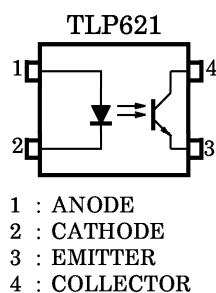
AC / DC - INPUT MODULE

SOLID STATE RELAY

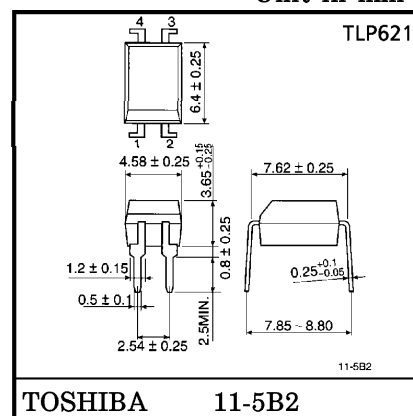
The TOSHIBA TLP621, -2, and -4 consists of a photo-transistor optically coupled to a gallium arsenide infrared emitting diode. The TLP621-2 offers two isolated channels in an eight lead plastic DIP, which the TLP621-4 provides four isolated channels in a sixteen plastic DIP.

- Collector-Emitter Voltage : 55V (Min.)
- Current Transfer Ratio : 50% (Min.)
- Rank GB : 100% (Min.)

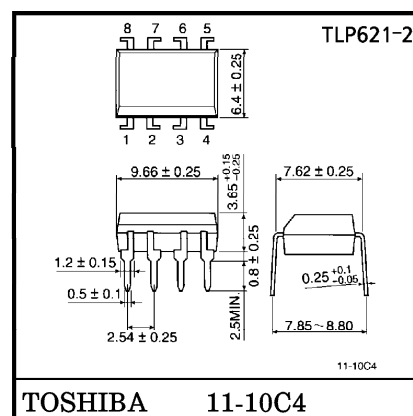
PIN CONFIGURATIONS (TOP VIEW)



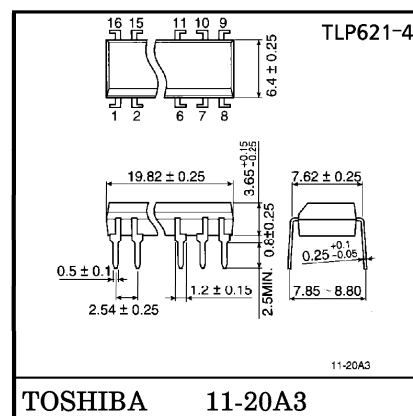
Unit in mm



Weight : 0.26g



Weight : 0.54g



Weight : 1.1g

● Current Transfer Ratio

TYPE	CLASSI- FICATION *1	CURRENT TRANSFER RATIO (%) (I _C / I _F)		MARKING OF CLASSIFICATION
		I _F =5mA, V _{CE} =5V, Ta=25°C		
		MIN.	MAX.	
TLP621	(None)	50	600	BLANK, Y, Y■, G, G■, B, B■, GB
	Rank Y	50	150	Y, Y■
	Rank GR	100	300	G, G■
	Rank BL	200	600	B, B■
	Rank GB	100	600	G, G■, B, B■, GB
TLP621-2	(None)	50	600	BLANK, GR, BL, GB
TLP621-4	Rank GB	100	600	GR, BL, GB

*1 : Ex. Rank GB : TLP621 (GB)

(Note) Application type name for certification test, please use standard product type name, i.e.

TLP621 (GB) : TLP621

TLP621-2 (GB) : TLP621-2

	MADE IN JAPAN		MADE IN THAILAND	
UL Recognized	E67349	*2	E152349	*2
BSI Approved	6508, 7445	*3	6505, 7445	*3
SEMKO Approved	9735090 / 01	*4	—	

*2 UL1577

*3 BS EN60065 : 1994, BS EN60950 : 1992

*4 EN60950 (Approved is TLP621 only)

- Option (D4) type

VDE Approved : DIN VDE0884/06.92, Certificate No. 68384

Maximum Operating Insulation Voltage : 890V_{PK}

Highest Permissible Over Voltage : 8000V_{PK}

(Note) When a VIDE0884 approved type is needed, please disignate the “Option (D4)”

	7.62mm pich standard type	10.16mm pich (LF2) type
● Creepage Distance	: 6.4mm (Min.)	8.0mm (Min)
Clearance	: 6.4mm (Min.)	8.0mm (Min)
Insulation Thickness	: 0.4mm (Min.)	0.4mm (Min)

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING		UNIT
			TLP621	TLP621-2 TLP621-4	
LED	Forward Current	I _F	60	50	mA
	Forward Current Derating	$\Delta I_F / ^\circ\text{C}$	-0.7 (Ta > 39°C)	-0.5 (Ta = 25°C)	mA / °C
	Pulse Forward Current	I _{FP}	1 (100 μ s pulse, 100pps)		A
	Power Dissipation	P _D	100	70	mW
	Power Dissipation Derating	$\Delta P_D / ^\circ\text{C}$	-1.0	-0.7	mW / °C
	Reverse Voltage	V _R	5		V
	Junction Temperature	T _j	125		°C
DETECTOR	Collector-Emitter Voltage	V _{CEO}	55		V
	Emitter-Collector Voltage	V _{ECO}	7		V
	Collector Current	I _C	50		mA
	Collector Power Dissipation (1 Circuit)	P _C	150	100	mW
	Collector Power Dissipation Derating (1 Circuit, Ta $\geq$ 25°C)	$\Delta P_C / ^\circ\text{C}$	-1.5	-1.0	mW / °C
	Junction Temperature	T _j	125		°C
Storage Temperature Range		T _{stg}	-55~125		°C
Operating Temperature Range		T _{opr}	-55~100		°C
Lead Soldering Temperature		T _{sol}	260 (10s)		°C
Total Package Power Dissipation		P _T	250	150	mW
Total Package Power Dissipation Derating (Ta $\geq$ 25°C)		$\Delta P_T / ^\circ\text{C}$	-2.5	-1.5	mW / °C
Isolation Voltage (Note 1)		BV _S	5000 (AC, 1min., R.H. $\leq$ 60%)		V _{rms}

(Note 1) Device considered a two terminal : LED side pins shorted together, and DETECTOR side pins shorted together.

RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT
Supply Voltage	V _{CC}	—	5	24	V
Forward Current	I _F	—	16	20	mA
Collector Current	I _C	—	1	10	mA
Operating Temperature	T _{opr}	-25	—	85	°C

INDIVIDUAL ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
LED	Forward Voltage	V_F	$I_F = 10\text{mA}$	1.0	1.15	1.3	V
	Reverse Current	I_R	$V_R = 5\text{V}$	—	—	10	μA
	Capacitance	C_T	$V = 0, f = 1\text{MHz}$	—	30	—	pF
DETECTOR	Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 0.5\text{mA}$	55	—	—	V
	Emitter-Collector Breakdown Voltage	$V_{(BR)ECO}$	$I_E = 0.1\text{mA}$	7	—	—	V
	Collector Dark Current	I_{CEO}	$V_{CE} = 24\text{V}$	—	10	100	nA
			$V_{CE} = 24\text{V}, T_a = 85^\circ\text{C}$	—	2	50	μA
	Capacitance (Collector to Emitter)	C_{CE}	$V = 0, f = 1\text{MHz}$	—	10	—	pF

COUPLED ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Current Transfer Ratio	I_C / I_F	$I_F = 5\text{mA}, V_{CE} = 5\text{V}$ Rank GB	50	—	600	%
			100	—	600	
Saturated CTR	$I_C / I_F (\text{sat})$	$I_F = 1\text{mA}, V_{CE} = 0.4\text{V}$ Rank GB	—	60	—	%
			30	—	—	
Collector-Emitter Saturation Voltage	$V_{CE} (\text{sat})$	$I_C = 2.4\text{mA}, I_F = 8\text{mA}$	—	—	0.4	V
		$I_C = 0.2\text{mA}, I_F = 1\text{mA}$ Rank GB	—	0.2	—	
			—	—	0.4	

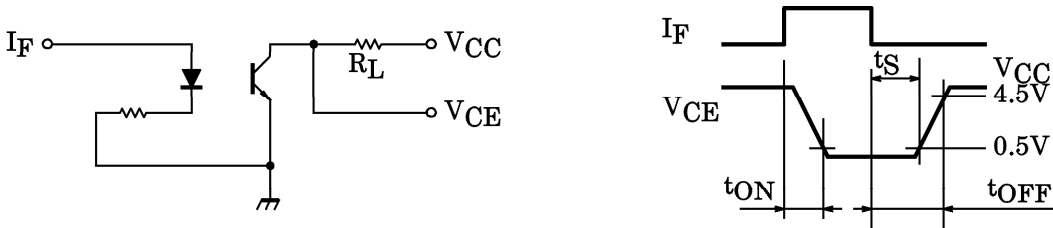
ISOLATION CHARACTERISTICS (Ta = 25°C)

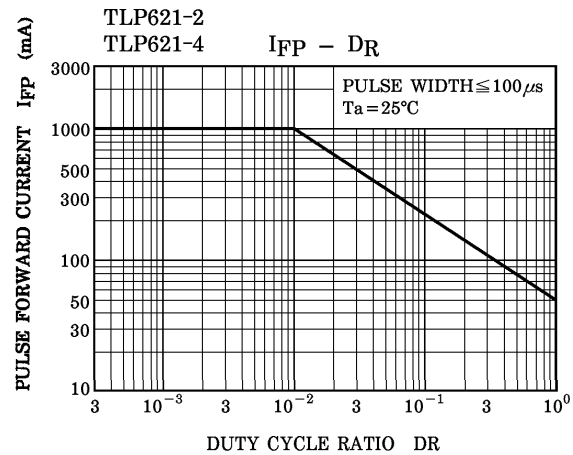
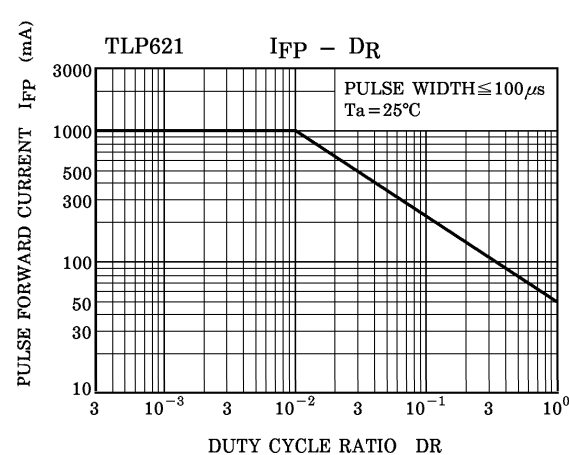
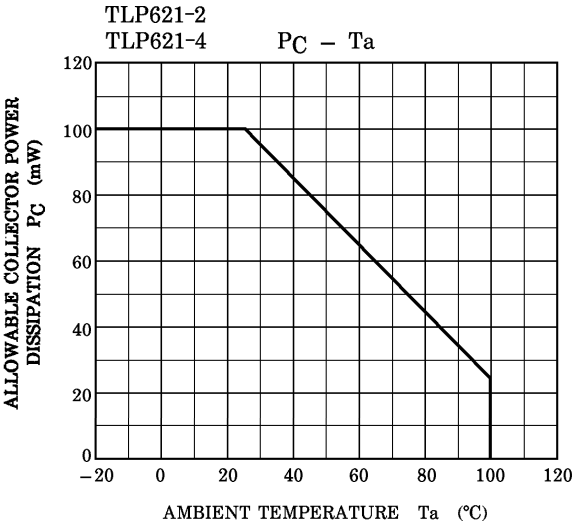
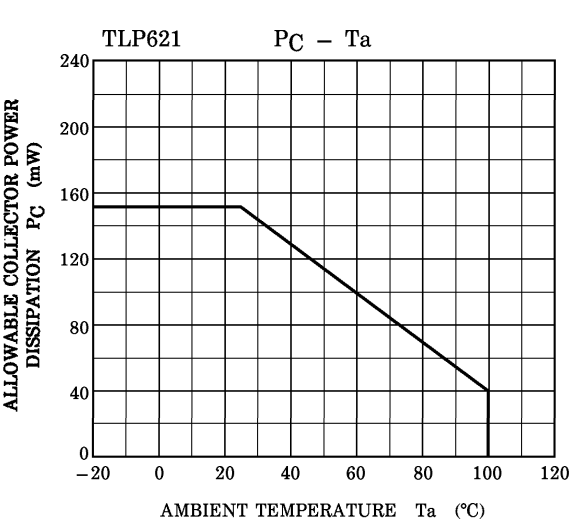
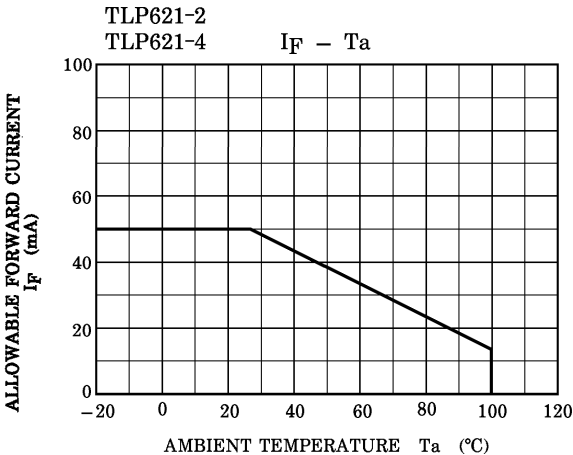
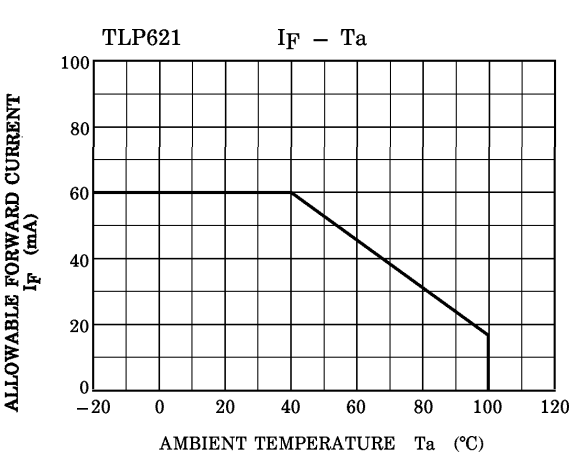
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Capacitance (Input to Output)	C_S	$V_S = 0, f = 1\text{MHz}$	—	0.8	—	pF
Isolation Resistance	R_S	$V_S = 500\text{V}$	1×10^{12}	10^{14}	—	Ω
Isolation Voltage	BV_S	AC, 1 minute	5000	—	—	V_{rms}
		AC, 1 second, in oil	—	10000	—	
		DC, 1 minute, in oil	—	10000	—	V_{dc}

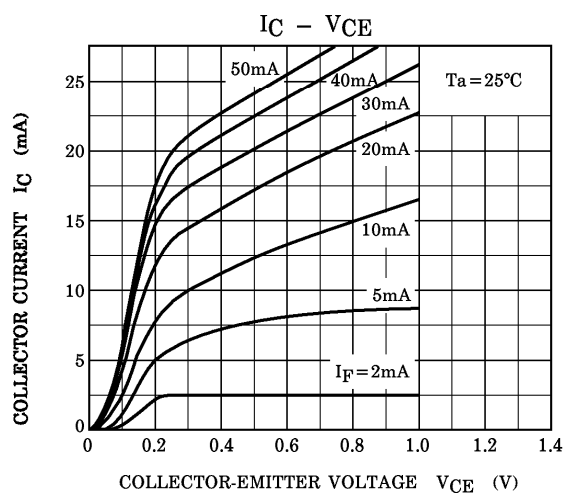
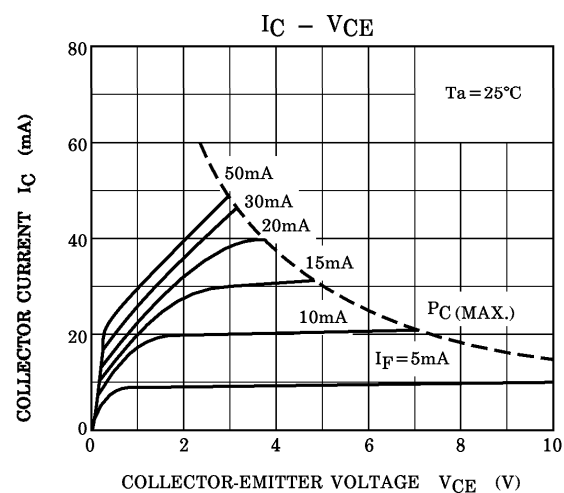
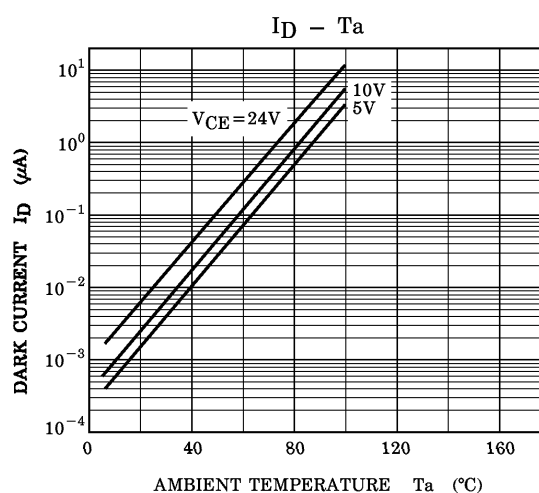
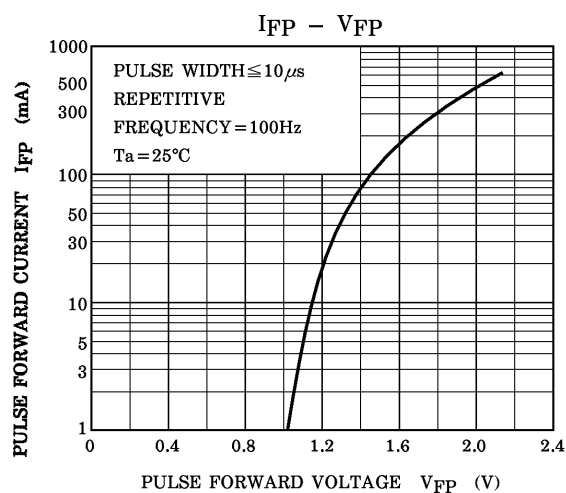
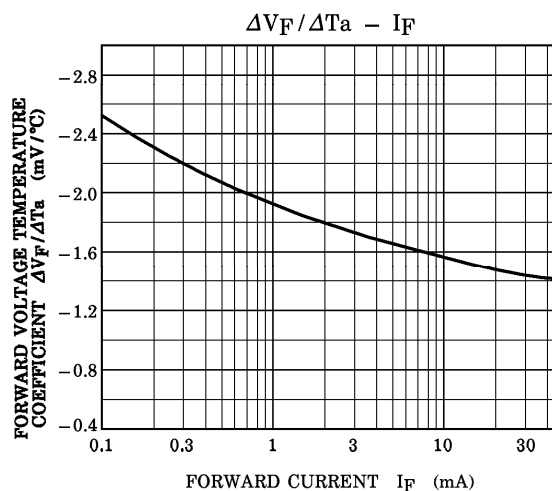
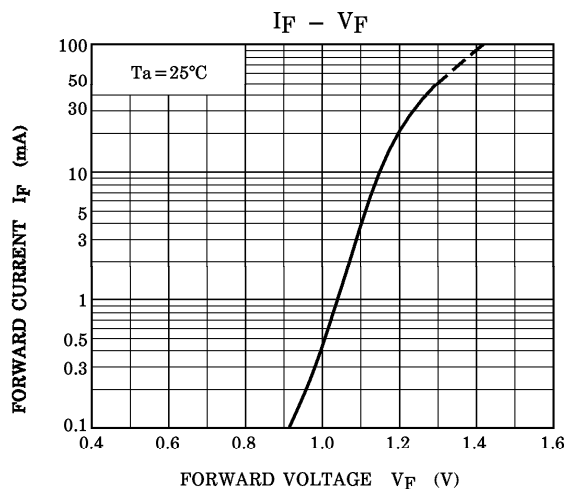
SWITCHING CHARACTERISTICS (Ta = 25°C)

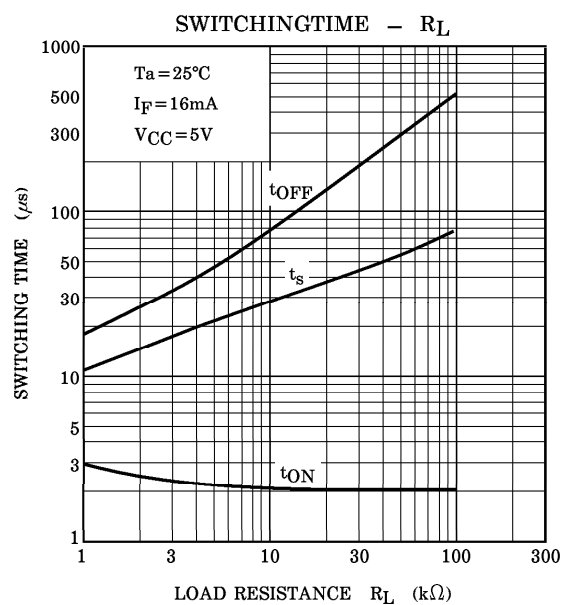
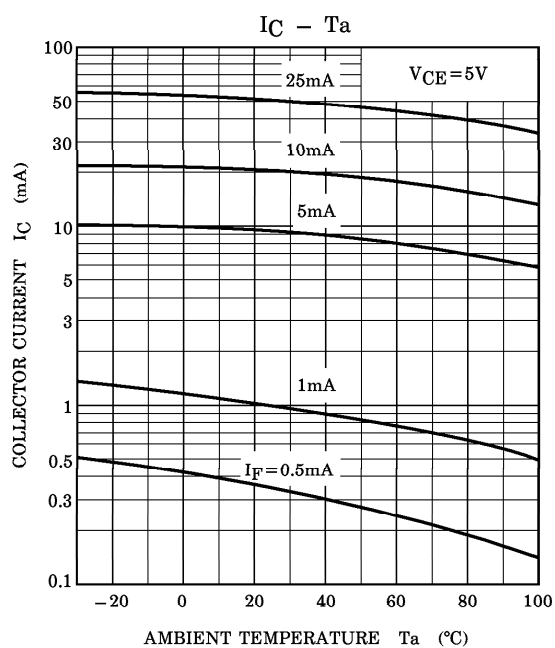
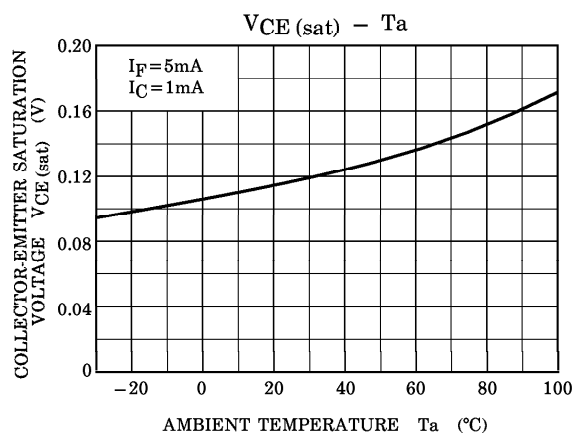
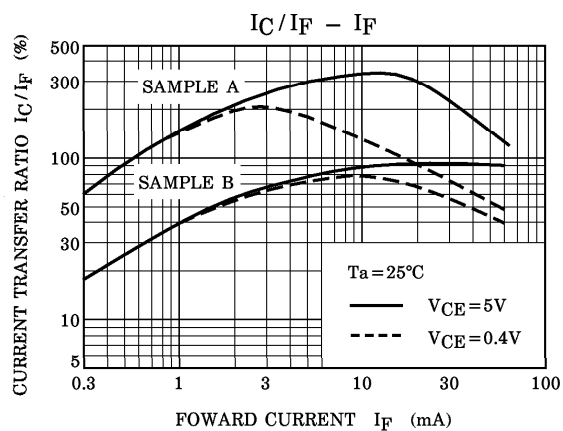
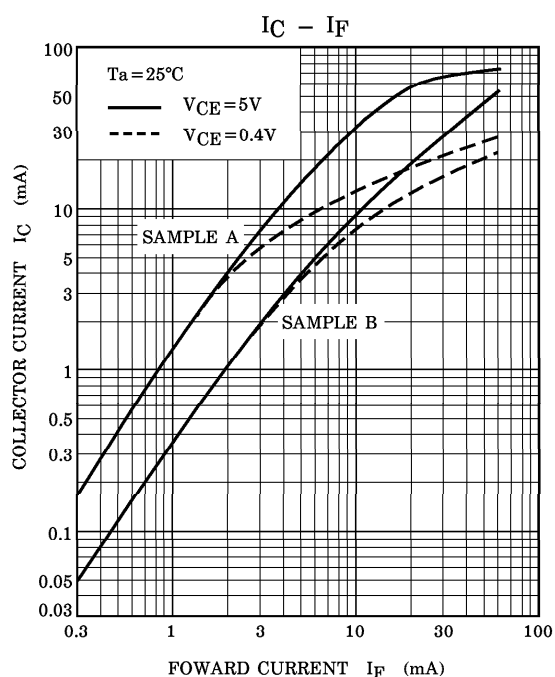
CHARACTERICTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Rise Time	t_r	$V_{CC}=10V, I_C=2mA$ $R_L=100\Omega$	—	2	—	μs
Fall Time	t_f		—	3	—	
Turn-on Time	t_{on}		—	3	—	
Turn-off Time	t_{off}		—	3	—	
Turn-on Time	t_{ON}	$R_L=1.9k\Omega$ (Fig.1) $V_{CC}=5V, I_F=16mA$	—	2	—	μs
Storage Time	t_S		—	15	—	
Turn-off Time	t_{OFF}		—	25	—	

Fig.1 SWITCHING TIME TEST CIRCUIT









RESTRICTIONS ON PRODUCT USE

000707EBC

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